

IN THE ABSTRACT:

Please replace the Abstract with the attached unnumbered page entitled "ABSTRACT OF THE DISCLOSURE".

IN THE CLAIMS:

5 Please cancel claims 1-8 on substitute pages 16 and 17, without prejudice, and add the following claims:

10 --9. A method for producing an integrated semiconductor component comprising the steps of preparing a semiconductor substrate having at least one first region and at least one second region; producing gate paths in the first region and the second region of the semiconductor substrate; producing source/drain regions neighboring the gate paths in the first region of the semiconductor substrate; forming at least two spacers on gate paths in the first region; producing source/drain regions neighboring the gate paths in the second region of the semiconductor substrate; forming sacrificial contacts in the second region before all spacers are formed in the first region; and preparing contacts to predetermined source/drain regions in the second region and the first region.--

15 --10. A method according to claim 9, wherein the spacers are formed of a material selected from a group consisting of silicon oxide, silicon nitride and oxynitride.--

20 --11. A method according to claim 9, wherein the step of producing gate paths includes applying a polysilicon layer on the semiconductor substrate, providing a protective layer selected from a group consisting of silicon nitride, silicon oxide